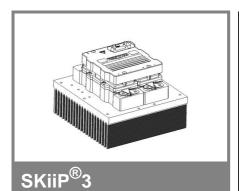
SKiiP 1213GB123-2DL V3



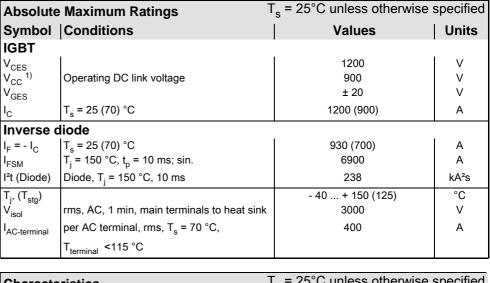
2-pack-integrated intelligent Power System

Power section SKiiP 1213GB123-2DL V3

Preliminary Data

Power section features

- SKiiP technology inside
- Trench IGBTs
- CAL HD diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP[®] 3 System)
- IEC 60068-1 (climate) 40/125/56)
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal
- 8) AC connection busbars must be connected by the user; copper busbars available on request

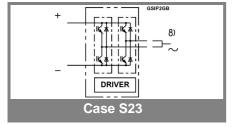


Characte	eristics	$T_{s} = 25^{\circ}$	T _s = 25°C unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units		
IGBT							
V _{CEsat}	I _C = 600 A, T _j = 25 (125) °C; measured at terminal		1,7 (1,9)	2,1	V		
V_{CEO}	T _i = 25 (125) °C; at terminal		0,9 (0,8)	1,1 (1)	V		
r _{CE}	T _i = 25 (125) °C; at terminal		1,3 (1,8)	1,7 (2,2)	mΩ		
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = V_{CES},$ $T_i = 25 (125) ^{\circ}\text{C}$		2,4 (72)				
$E_{on} + E_{off}$	$I_{\rm C}^{\rm J}$ = 600 A, $V_{\rm CC}$ = 600 V		221				
	T_{j} = 125 °C, V_{CC} = 900 V		390		mJ		
R _{CC+EE}	terminal chip, T _i = 25 °C		0,25				
L _{CE}	top, bottom		6		nΗ		
C_{CHC}	per phase, AC-side		3,4		nF		
Inverse o	diode						
$V_F = V_{EC}$	I_F = 600 A, T_j = 25 (125) °C measured at terminal		1,5 (1,5)	1,8	V		
V_{TO}	T _i = 25 (125) °C		0,9 (0,7)	1,1 (0,9)	V		
r _T	T _i = 25 (125) °C		1 (1,3)	1,1 (1,5)	mΩ		
Ė _{rr}	$I_{\rm C}$ = 600 A, $V_{\rm CC}$ = 600 V		42		mJ		
	T_{j} = 125 °C, V_{CC} = 900 V		56		mJ		
Mechani	cal data						
M_{dc}	DC terminals, SI Units	6		8	Nm		
M _{ac}	AC terminals, SI Units	13		15	Nm		
W	SKiiP® 3 System w/o heat sink		1,7		kg		
w	heat sink		5,4		kg		

reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)

Region | Dec IGBT | 0.03 | K/W

$R_{th(j-s)l}$	per IGB	Т					0,03	K/W
$R_{th(j-s)D}$	per diod	е					0,058	K/W
Z_{th}	R _i (mK/V	V) (max. valu	ıes)			tau	_i (s)	
	1	2	3	4	1	2	3	4
$Z_{th(j-r)I}$	9,8	16,4	3,8	0	0,37	0,06	0,01	1
$Z_{th(j-r)D}$	10	24	24	36	50	5	0,25	0,04
Z _{th(r-a)}	4,3	20,3	7,1	2,3	160	53	9	0,4



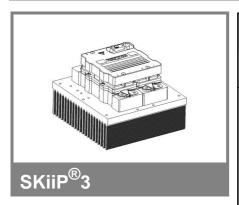
^{*} The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of

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2-pack-integrated intelligent Power System

2-pack integrated gate driver SKiiP 1213GB123-2DL V3

Preliminary Data

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature
- · Short circuit protection
- · Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- · Interlock of top/bottom switch
- Isolation by transformers
- Fibre optic interface (option for GB-types only)
- IEC 60068-1 (climate) 40/85/56

Absolute	Maximum Ratings	T _a = 25°C unless otherwise specified		
Symbol	Conditions	Values	Units	
V_{S2}	unstabilized 24 V power supply	30	V	
V_{i}	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
V_{isollO}	input / output (AC, rms, 2s)	3000	V	
V _{isoIPD}	partial discharge extinction voltage, rms, Q _{PD} ≤10 pC;	1170	V	
V _{isol12}	output 1 / output 2 (AC, rms, 2s)	1500	V	
f _{sw}	switching frequency	15	kHz	
f _{out}	output frequency for I _{peak(1)} =I _C	15	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C	

Characte	eristics	(T _a = 25 °C)			
Symbol	Conditions	min.	typ.	max.	Units
V_{S2}	supply voltage non stabilized	13	24	30	V
I _{S2}	$V_{S2} = 13V - 30V$	10mA+29*f/kHz+0,00023*(I _{AC} /A) ²			mA
V _{iT+}	input threshold voltage (High)			12,3	V
V_{iT-}	input threshold voltage (Low)	4,6			V
R _{IN}	input resistance		10		kΩ
C_{IN}	input capacitance		1		nF
t _{d(on)IO}	input-output turn-on propagation time		1,4		μs
t _{d(off)IO}	input-output turn-off propagation time		1,4		μs
$t_{pERRRESET}$	error memory reset time		12,2		μs
t_{TD}	top / bottom switch interlock time		3,3		μs
I _{analogOUT}	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		1200		Α
I _{s1out}	max. load current			50	mA
I _{TRIPSC}	over current trip level				
	(I _{analog} OUT = 10 V)		1500		Α
T_tp	over temperature protection	110		120	°C
U _{DCTRIP}	U_{DC} -protection ($U_{analog OUT} = 9 V$);	i	not mplemented	d	V
	(option for GB types)				

For electrical and thermal design support please use SEMISEL. Access to SEMISEL is via SEMIKRON website http://www.semikron.com.

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